PN3638 / PN3638A

Discrete POWER & Signal **Technologies**



PN3638 PN3638A



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 500 mA. Sourced from Process 63. See PN2907A for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CEO}	Collector-Emitter Voltage	25	V	
Vсво	Collector-Base Voltage	25	V	
V _{EBO}	Emitter-Base Voltage	4.9	V	
lc	Collector Current - Continuous	800	mA	
TJ, Tstg	Operating and Storage Junction Temperature Range	-55 to +150	°C	

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES: 1) These ratings are based on a maximum junction temperature of 150 degrees C. 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах	Units
		PN3638/A	
PD	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

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(continue			PNP Gene		
			= 25°C unless otherwise noted	ical Characteristics TA	Electr
Units	Max	Min	Test Conditions	Parameter	Symbol
				RACTERISTICS	OFF CHA
V		25	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	Collector-Emitter Breakdown Voltage*	V _{(BR)CEO}
V		25	$I_{\rm C} = 100 \ \mu A, \ I_{\rm B} = 0$	Collector-Emitter Breakdown Voltage*	V _{(BR)CES}
V		25	$I_{\rm C} = 10 \ \mu A, \ I_{\rm E} = 0$	Collector-Base Breakdown Voltage	V(BR)CBO
V		4.0	$I_E = 10 \ \mu A, \ I_C = 0$	Emitter-Base Breakdown Voltage	V _{(BR)EBO}
nA μA	35 2.0		$V_{CE} = 15 \text{ V}, I_E = 0$ $V_{CE} = 15 \text{ V}, I_E = 0, T_A = 65^{\circ}\text{C}$	Collector-Cutoff Current	ICES
				RACTERISTICS*	ON CHAF
			$V_{CE} = 1.0 \text{ V}, I_{C} = 50 \text{ mA}$	DC Current Gain	h _{FE}
		30 100	PN3638		
		100	PN3638A V _{CE} = 2.0 V, I _C = 300 mA		
		30	PN3638		
		20	PN3638A		
		20	V _{CE} = 10 V, I _C = 100 mA PN3638		
		80	PN3638A		
		100	V _{CE} = 10 V, I _C = 1.0 mA PN3638A		
V	0.25	100	$I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 2.5 \text{ mA}$	Collector-Emitter Saturation Voltage	V _{CE(sat)}
V	1.0		$I_{\rm C} = 300 \text{ mA}, I_{\rm B} = 30 \text{ mA}$		VCE(Sal)
V V	1.1 2.0	0.8	$I_{C} = 50 \text{ mA}, I_{B} = 2.5 \text{ mA}$ $I_{C} = 300 \text{ mA}, I_{B} = 30 \text{ mA}$	Base-Emitter Saturation Voltage	V _{BE(sat)}
	2.0	0.0			
				IGNAL CHARACTERISTICS	
pF	20		V _{CB} = 10 V, f = 1.0 MHz PN3638	Output Capacitance	Cob
pF	10		PN3638A		
_			$V_{BE} = 0.5 V, f = 1.0 MHz$	Input Capacitance	Cib
pF pF	65 25		PN3638 PN3638A		
Ч	20		$I_{\rm C} = 50 \text{ mA}, V_{\rm CE} = 3.0 \text{ V},$	Small-Signal Current Gain	h _{fe}
		1.0	f = 100 MHz PN3638		10
		1.5	PN3638A I _C = 10 mA, V _{CE} = 10 V,		
		25	f = 1.0 kHz PN3638		
		100	PN3638A		
kΩ	2.0		$I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V},$	Input Impedance	h _{ie}
µmhos -4	1.2		f = 1.0 kHz	Output Admittance	h _{oe}
x10 ⁻⁴ x10 ⁻⁴	26 15		PN3638 PN3638A	Voltage Feedback Ratio	h _{re}
				NG CHARACTERISTICS	SWITCH
ns		75	V _{CC} = 10 V, I _C = 300 mA,	Turn-on Time	ton
ns		20	$I_{B1} = 30 \text{ mA}$	Delay Time	ta
ns		70		Rise Time	ua tr
		170	V _{CC} = 10 V, I _C = 300 mA	Turn-off Time	loff
ns					-011
ns ns		140	$I_{B1} = I_{B2} = 30 \text{ mA}$	Storage Time	ts

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